

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A sputtering target consisting essentially of Si,
wherein the target comprises Si sintered material having a relative density in a range of 70% or more and 95% or less, and
wherein a ratio ($I_{(111)}/I_{(220)}$) of peak intensity ($I_{(111)}$) of (111) face to peak intensity ($I_{(220)}$) of (220) face of Si is in a range of 1.8 ± 0.3 when a sputtering surface of the target is measured for crystal face orientation by X-ray diffractometry.
2. (Cancelled)
3. (Original) The sputtering target according to claim 1, having hardness in a range of Hv 300 or more and Hv 800 or less in terms of Vickers hardness.
4. (Withdrawn) A sputtering target consisting essentially of Si, wherein the target comprises an Si sintered material having a relative density in a range of 70 % or more and 95 % or less.
5. (Withdrawn) A sputtering target consisting essentially of Si, wherein the target has hardness in a range of Hv 300 or more and Hv 800 or less in terms of Vickers hardness.
6. (Withdrawn) The sputtering target according to claim 5, wherein the target as a whole has dispersion of the Vickers hardness within 30 %.
7. (Withdrawn) The sputtering target according to claim 5, comprising an Si sintered material having a relative density in a range of 70 % or more and 95 % or less.
8. (Withdrawn) A sputtering target consisting essentially of Si, wherein an oxygen content of the target is in a range of 0.01 mass% or more and 1 mass% or less.

9. (Withdrawn) The sputtering target according to claim 8, comprising an Si sintered material having a relative density in a range of 70 % or more and 95 % or less.
10. (Previously Presented) The sputtering target according to claim 1, which is a target for forming an oxide film.
11. (Previously Presented) The sputtering target according to claim 1, which is used as a target for forming an optical thin film.
12. (Withdrawn) A process for producing an Si oxide film, comprising forming an Si oxide film by sputtering the sputtering target according to claim 1 in an oxygen-containing atmosphere.
13. (Withdrawn) The process for producing an Si oxide film according to claim 12, wherein the Si oxide film is an optical thin film.
14. (New) The sputtering target according to claim 1, wherein the sputtering target has a sintered structure.